

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$ (Max.)	I _D (A) ^a Q _g (Typ							
30	0.018 at V _{GS} = 10 V	12							
	0.020 at V _{GS} = 6 V	12	5 nC						
	0.022 at V _{GS} = 4.5 V	12							

PowerPAK SC-70-6L-Single 2.05 mm **Bottom View**

Ordering Information:

SiA462DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Material categorization: For definitions of compliance please see

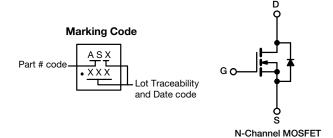
www.vishav.com/doc?99912



COMPLIANT HALOGEN FREE

APPLICATIONS

- DC/DC Converters and Synchronous Buck Converters
 - Lower Ringing Voltage from Soft Turn-On
 - High Efficiency from Fast Turn-Off
 - Lower Shoot-Through Possibility



ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unle	ess otherwise i	noted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	± 20	V	
	T _C = 25 °C		12 ^a		
Continuous Drain Current /T 150 °C\	T _C = 70 °C	,	12 ^a		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	12 ^{a,b, c}		
	T _A = 70 °C		9.7 ^{b, c}	Α	
Pulsed Drain Current (t = 300 μs)	•	I _{DM}	40		
Continuous Source-Drain Diode Current	T _C = 25 °C	I-	12 ^a		
Continuous Source-Drain Diode Current	T _A = 25 °C	l _S	2.9 ^{b, c}		
	T _C = 25 °C		19		
Mariana Parray Dissination	T _C = 70 °C	Б	12	14/	
Maximum Power Dissipation	T _A = 25 °C	- P _D	3.5 ^{b, c}	W	
	T _A = 70 °C		2.2 ^{b, c}		
Operating Junction and Storage Temperature Ra	nge	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature	e) ^{d, e}		260	10	

THERMAL RESISTANCE RATINGS										
Parameter		Symbol	Typical	Maximum	Unit					
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W					
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	5.3	6.5	O/ VV					

Notes:

- a. Based on package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishav.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

Document Number: 63269 S13-0628-Rev. A, 25-Mar-13 For technical questions, contact:: pmostechsupport@vishay.com



SPECIFICATIONS ($T_J = 25 ^{\circ}\text{C}$,	1					1
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static Drain Course Breakdown Valters	T V T	V _{GS} = 0 V, I _D = 250 μA	00		l	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30	0.4		V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		34		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	V V 1 050 A		- 5		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.2		2.4	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
	555	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	ļ ·
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α
		$V_{GS} = 10 \text{ V}, I_D = 9 \text{ A}$		0.015	0.018	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 6 \text{ V}, I_D = 7 \text{ A}$		0.016	0.020	Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 7 \text{ A}$		0.018	0.022	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 9 A		35		S
Dynamic ^b						
Input Capacitance	C _{iss}			570		
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		126		pF
Reverse Transfer Capacitance	C _{rss}	53 - 7 ds - 7		52		
Tievelse Transler Capacitation	9188	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 12 A		11	17	nC
Total Gate Charge	Q_g Q_gs	V _{DS} = 10 V, V _{GS} = 10 V, I _D = 12 N		5	7.5	
Gate-Source Charge		$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 12 \text{ A}$		1.7	7.0	
Gate-Drain Charge	Q _{gd}	VDS = 10 V, VGS = 1.0 V, ID = 12 / V		1.6		1
Gate Resistance	R _g	f = 1 MHz	0.2	1.0	2	Ω
Turn-On Delay Time	·	1 – 1 101112	0.2	5	10	22
Rise Time	t _{d(on)}	V 15VD 150		10	20	_
	+ -	V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_q = 1 Ω				
Turn-Off Delay Time	t _{d(off)}	1D = 1071, VGEN = 10 V, Hg = 132		15	30	
Fall Time	t _f			10	20	ns
Turn-On Delay Time	t _{d(on)}			12	25	-
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_L = 1.5 \Omega$		15	30	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		15	30	
Fall Time	t _f			10	20	
Drain-Source Body Diode Characteristic		7 27 20		T		<u> </u>
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			12	Α
Pulse Diode Forward Current ^a	I _{SM}				40	
Body Diode Voltage	V_{SD}	I _S = 10 A		0.85	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			20	40	ns
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 10 A, dl/dt = 100 A/μs, T _J = 25 °C		11	20	nC
Reverse Recovery Fall Time	ta	$_{1F} = 10 \text{ A}, \text{ u//ut} = 100 \text{ A/}\mu\text{s}, \text{ I}_{J} = 25 ^{\circ}\text{C}$		12		
Reverse Recovery Rise Time	t _b			8	İ	ns

Notes:

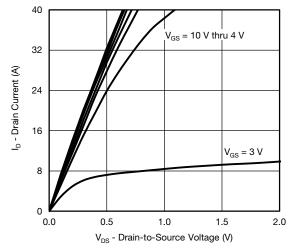
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

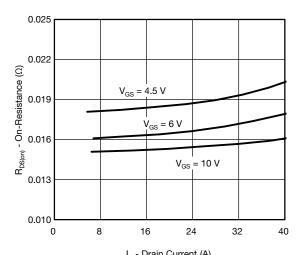
b. Guaranteed by design, not subject to production testing.



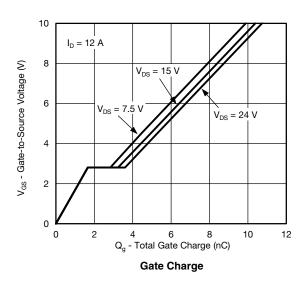
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

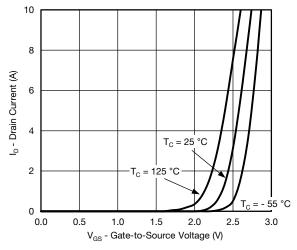


Output Characteristics

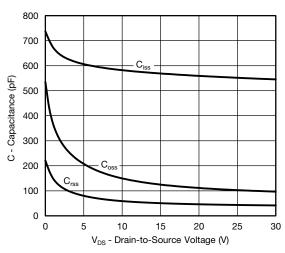


 $\rm I_D$ - Drain Current (A) On-Resistance vs. Drain Current and Gate Voltage

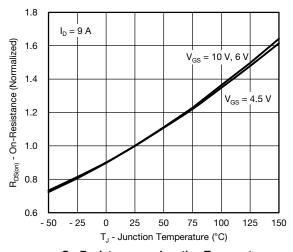




Transfer Characteristics



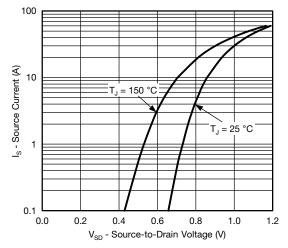
Capacitance



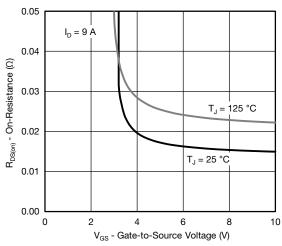
On-Resistance vs. Junction Temperature

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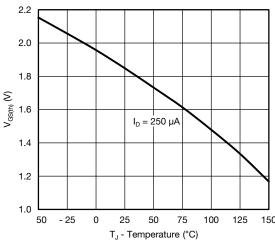
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



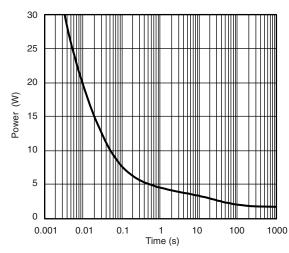
Source-Drain Diode Forward Voltage



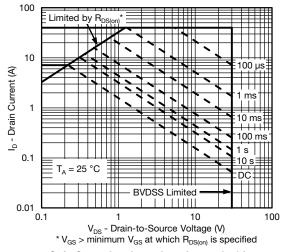
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



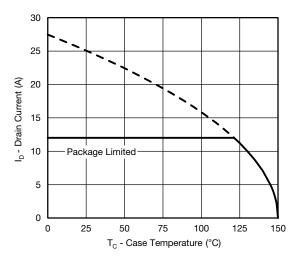
Single Pulse Power, Junction-to-Ambient



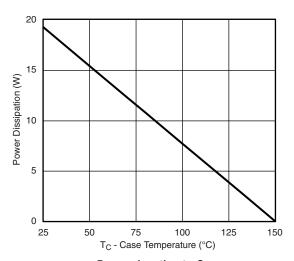
Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*

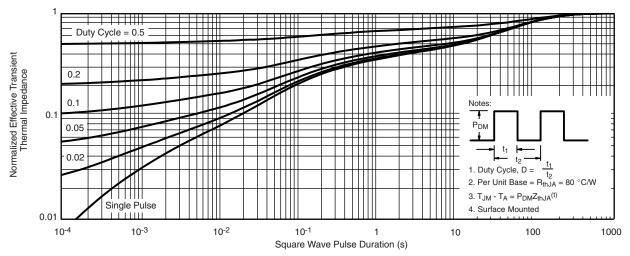


Power, Junction-to-Case

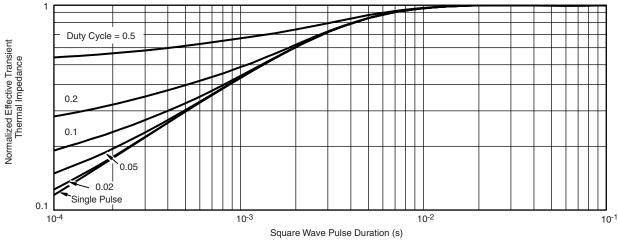
 $^{^{\}star}$ The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



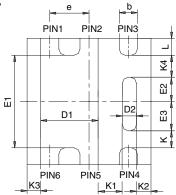
Normalized Thermal Transient Impedance, Junction-to-Case

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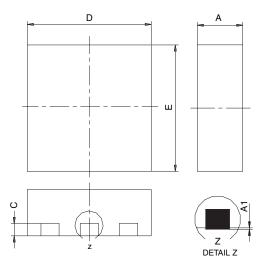
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

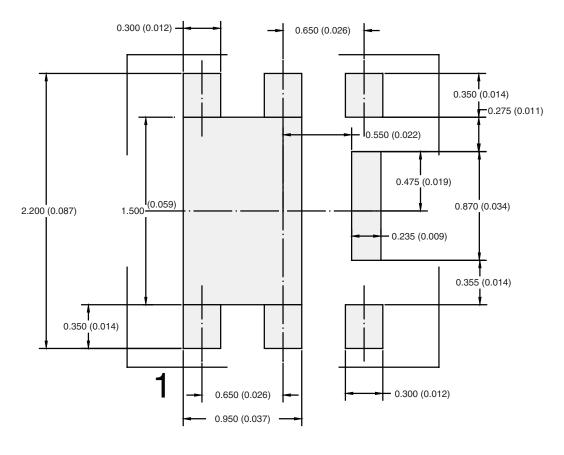
	SINGLE PAD						DUAL PAD						
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC			
K		0.275 TYP	١		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	١		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP	١	0.009 TYP			0.252 TYP			0.010 TYP			
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP		0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 – Bey C 06-Aug-07													

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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